Alfa-MOS
Technology

AFP3497

20V P-Channel
Enhancement Mode MOSFET

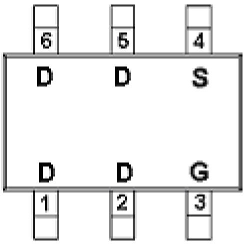
General Description

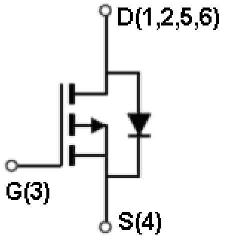
AFP3497, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.
These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

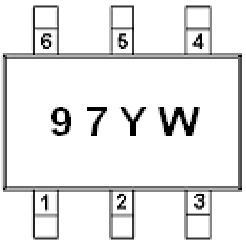
Features

- -20V/-3.8A,$R_{DS(ON)}$=100mΩ@V_{GS}=-4.5V
- -20V/-2.6A,$R_{DS(ON)}$=140mΩ@V_{GS}=-2.5V
- -20V/-1.5A,$R_{DS(ON)}$=190mΩ@V_{GS}=-1.8V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- Exceptional on-resistance and maximum DC current capability
- TSOP-6 package design

Pin Description (TSOP-6)







Application

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- Net Working System

Pin Define

Pin	Symbol	Description
1	D	Drain
2	D	Drain
3	G	Gate
4	S	Source
5	D	Drain
6	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP3497TS6RG	97YW	TSOP-6	Tape & Reel	3000 EA

※ 97 parts code
※ Y year code (0 ~ 9)
※ W week code (A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52)
※ AFP3497TS6RG : 7” Tape & Reel ; Pb- Free ; Halogen –Free

Absolute Maximum Ratings

(T_A=25℃ Unless otherwise noted)

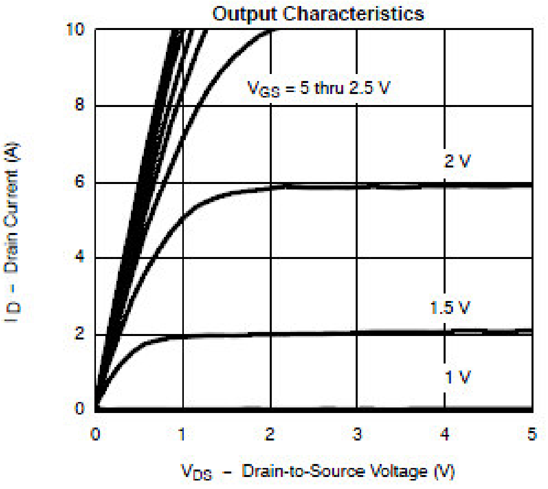
Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	-20	V
Gate –Source Voltage		V_{GSS}	±12	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	-3.8	A
	T_A=70℃		-2.6	
Pulsed Drain Current		I_{DM}	-20	A
Continuous Source Current(Diode Conduction)		I_S	-1.7	A
Power Dissipation	T_A=25℃	P_D	2.0	W
	T_A=70℃		1.3	
Operating Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	120	℃/W

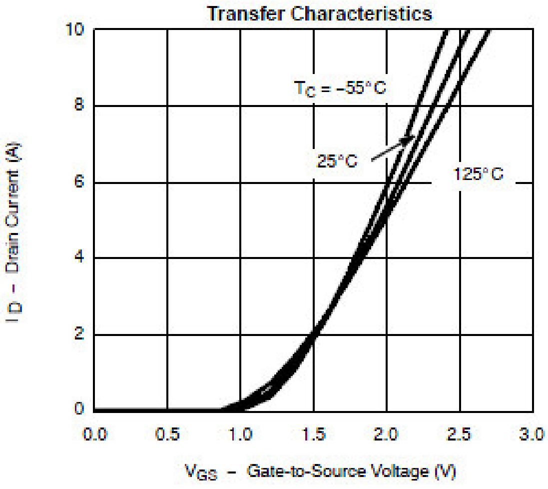
Electrical Characteristics

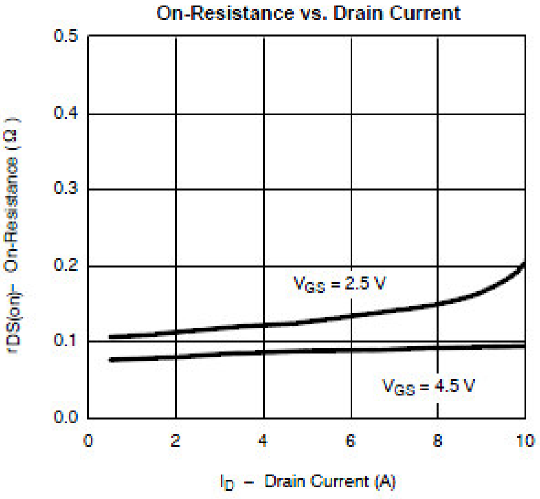
(T_A=25℃ Unless otherwise noted)

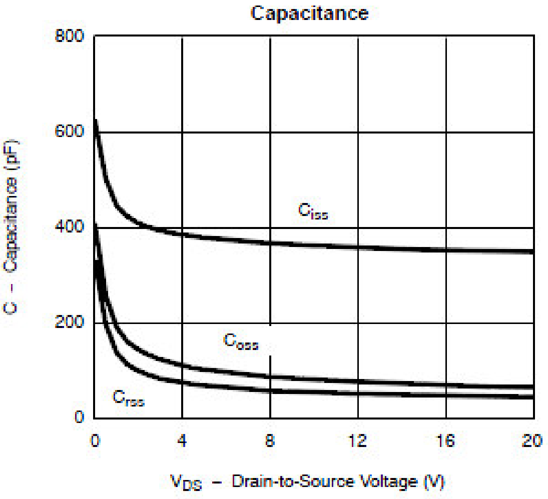
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-250uA	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250uA	-0.3		-0.7	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±12V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-16V,V_{GS}=0V			-1	uA
		V_{DS}=-16V,V_{GS}=0V T_J=85℃			-30	
On-State Drain Current	$I_{D(on)}$	V_{DS}≦-5V,V_{GS}=-4.5V	-6			A
		V_{DS}≦-5V,V_{GS}=-2.5V	-3			
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-4.5V,I_D=-3.8A		90	100	mΩ
		V_{GS}=-2.5V,I_D=-2.6A		124	140	
		V_{GS}=-1.8V,I_D=-1.5A		170	190	
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-2.8A		6.5		S
Diode Forward Voltage	V_{SD}	I_S=-1.25A,V_{GS}=0V		-0.75	-1.3	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=-6V,V_{GS}=-4.5V I_D≡-2.8A		5.8	10	nC
Gate-Source Charge	Q_{gs}			0.85		
Gate-Drain Charge	Q_{gd}			1.7		
Input Capacitance	C_{iss}	V_{DS}=-6V,V_{GS}=0V f=1MHz		415		pF
Output Capacitance	C_{oss}			223		
Reverse Transfer Capacitance	C_{rss}			87		
Turn-On Time	$t_{d(on)}$	V_{DD}=-6V,R_L=6Ω I_D≡-1.0A,V_{GEN}=-4.5V R_G=6Ω		13	25	ns
	t_r			36	60	
Turn-Off Time	$t_{d(off)}$			42	70	
	t_f			34	60	

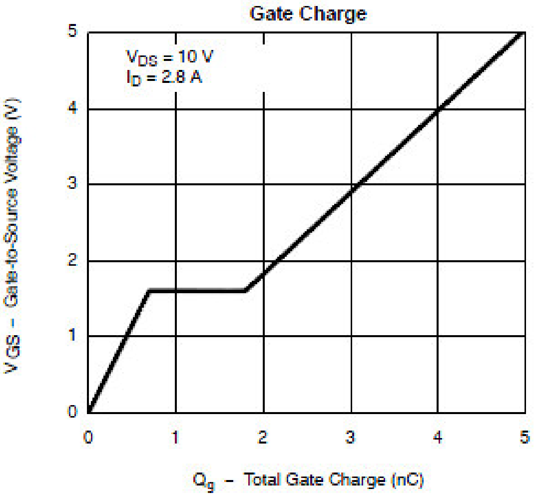
Typical Characteristics

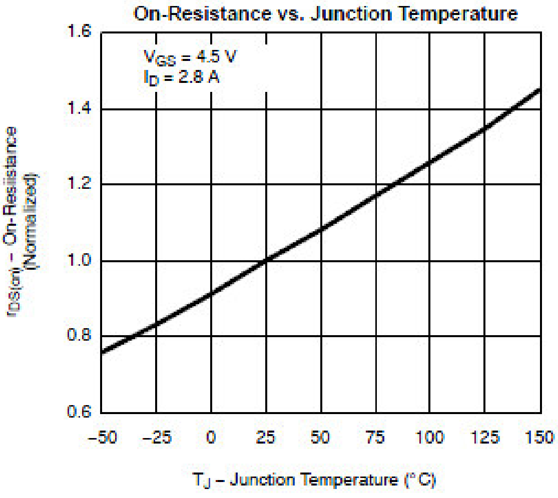

Output Characteristics


Transfer Characteristics


On-Resistance vs. Drain Current

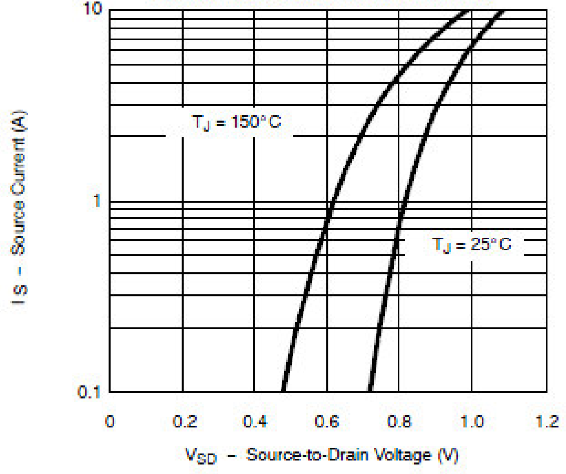

Capacitance


Gate Charge

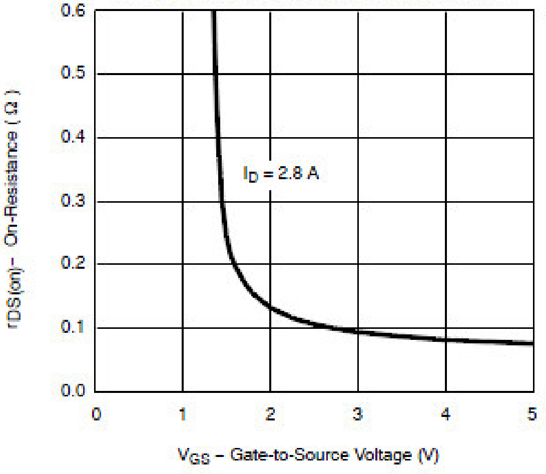

On-Resistance vs. Junction Temperature

Typical Characteristics

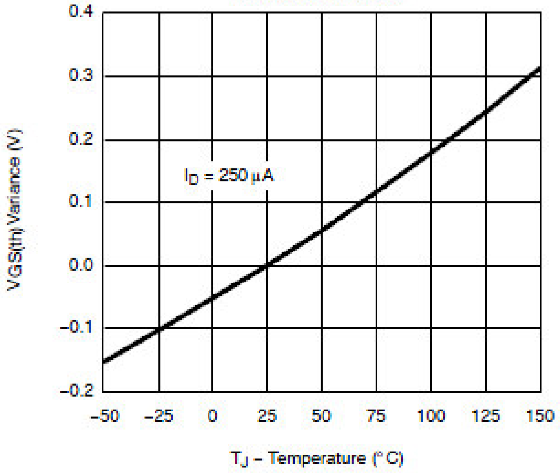
Source-Drain Diode Forward Voltage



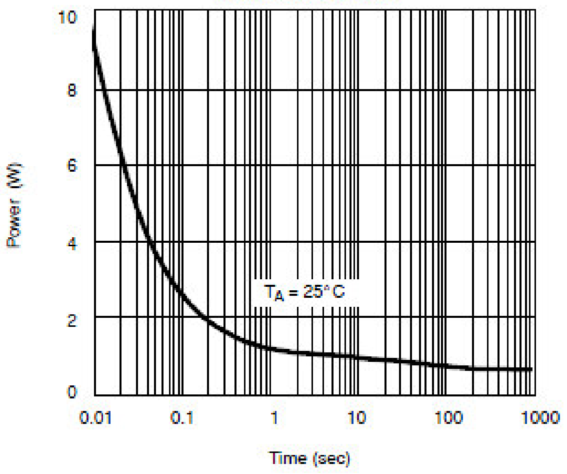
On-Resistance vs. Gate-to-Source Voltage



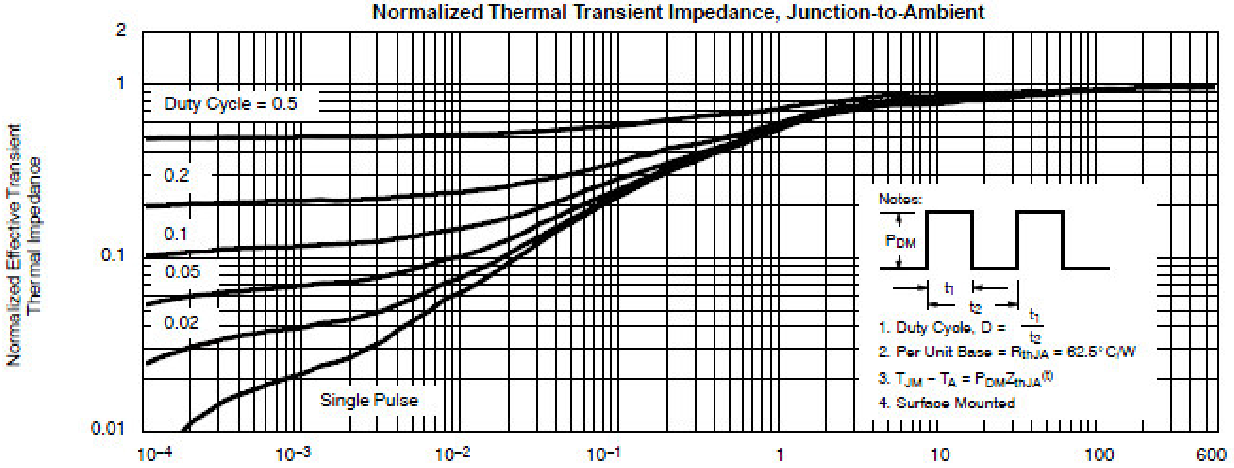
Threshold Voltage



Single Pulse Power

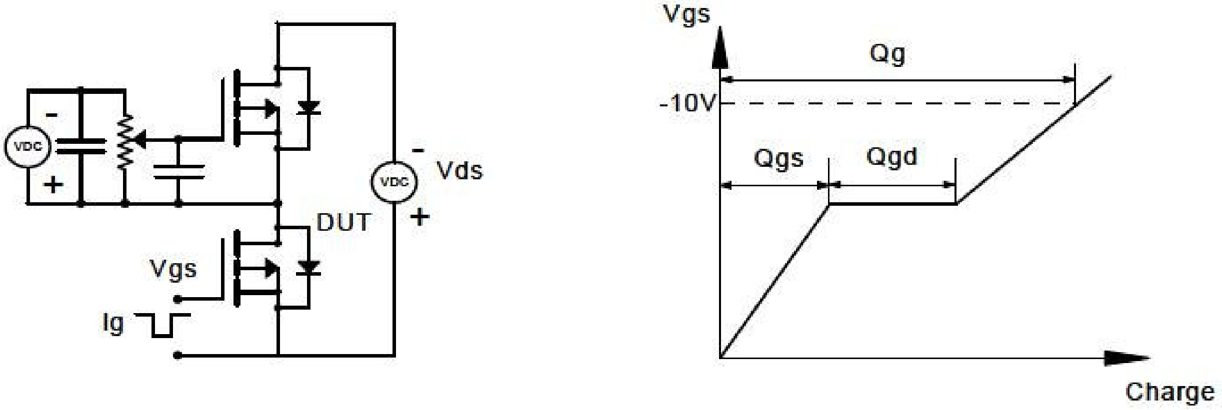


Normalized Thermal Transient Impedance, Junction-to-Ambient

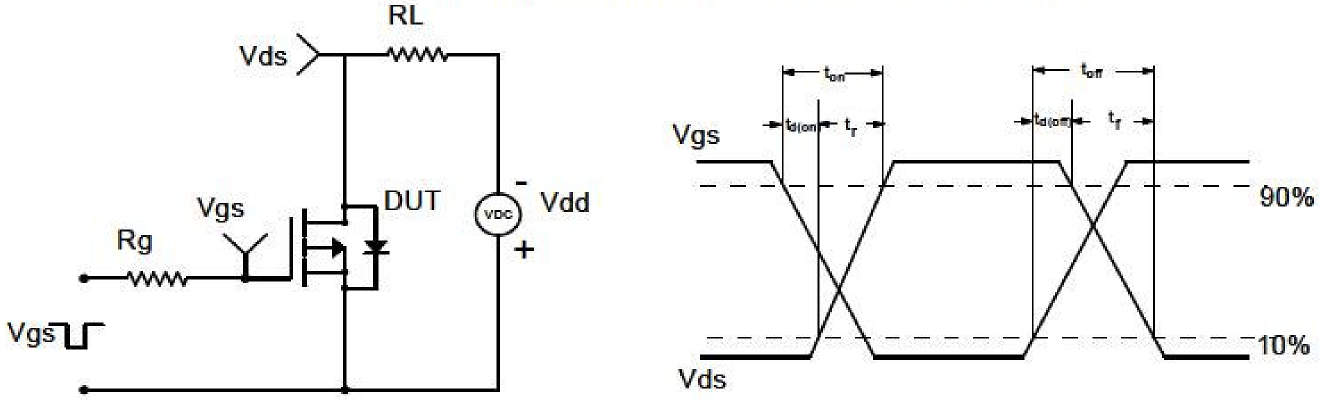


Typical Characteristics

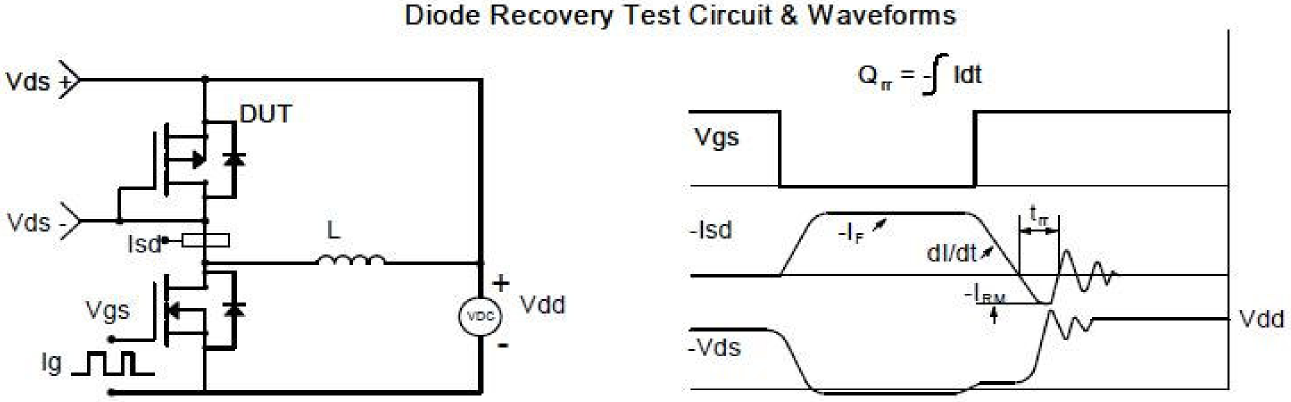
Gate Charge Test Circuit & Waveform



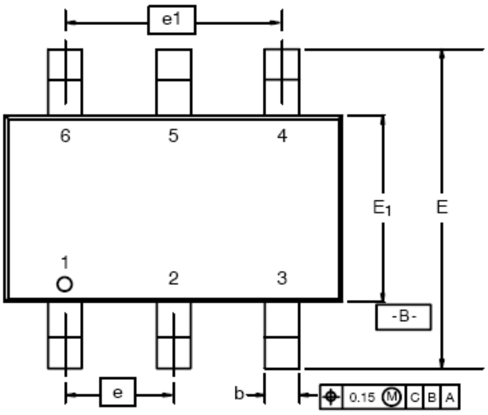
Resistive Switching Test Circuit & Waveforms

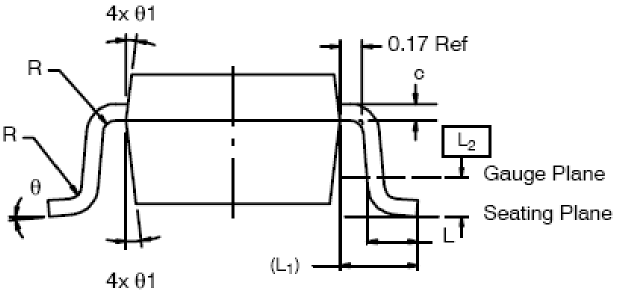


Diode Recovery Test Circuit & Waveforms



Package Information (TSOP-6)





Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A_1	0.01	-	0.10	0.0004	-	0.004
A_2	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E_1	1.55	1.65	1.70	0.061	0.065	0.067
e	1.00 BSC			0.0394 BSC		
e_1	1.90	2.00	2.10	0.075	0.080	0.085
L	0.35	-	0.50	0.014	-	0.020
L_1	0.60 Ref			0.024 Ref		
L_2	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
$θ_1$	7° Nom			7° Nom		

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